



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Yi Ding  
Assignee: Mosel Vitelic, Inc.  
Title: Nonvolatile Memory Cell With Multiple Floating Gates Formed After  
The Select Gate And Having Upward Protrusions  
Application No.: 10/632,186 Filing Date: July 30, 2003  
Examiner: Unassigned Group Art Unit: Unassigned  
Docket No.: M-15241 US

San Jose, California  
April 16, 2004

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR § 1.97(b)**

Dear Sir:

Pursuant to 37 CFR § 1.56, § 1.97 and § 1.98, the documents listed on the accompanying form PTO-1449 are called to the attention of the Examiner for the above patent application. Copies of these documents are enclosed.

Citation of these documents shall not be construed as:

1. an admission that the documents are necessarily prior art with respect to the instant invention;
2. a representation that a search has been made, other than as described above; or
3. an admission that the information cited herein is, or is considered to be material to patentability as defined in § 1.56(b).

No fee is believed to be required. If a fee is required for this Information Disclosure Statement, please charge the fee to Deposit Account No. 50-2257. This paper is being submitted in duplicate.

I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on April 16, 2004.

*Michael Shenker* 4-16-04  
Attorney for Applicant Date of Signature

Respectfully submitted,

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U.S. Department of Commerce, Patent and Trademark Office				Atty Docket No.		Serial No.		
				M-15241 US		10/632,186		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Applicant				
(Use several sheets if necessary)				Yi Ding				
				Filing Date		Group		
				July 30, 2003		Unassigned		
U.S. Patent Documents								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
	AA	6,420,231	16 Jul. 2002	Harari et al.				
	AB	2003/0218908 A1	27 Nov. 2003	Park et al.				
	AC	2004/0004863 A1	8 Jan. 2004	Wang				
	AD							
	AE							
	AF							
	AG							
	AH							
Foreign Patent Documents								
							Translation	
		Document	Date	Country	Class	Subclass	Yes	No
	AI	EP 0 938 098 A2	25 Aug. 1999	Europe				
	AJ							
	AK							
	AL							
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)								
	AM	United States Patent Application No. 10/798,475, entitled "Fabrication of Conductive Lines Interconnecting Conductive Gates in Nonvolatile Memories and Non-Volatile Memory Structures," Filed on March 10, 2004; Attorney Docket No. M-15296 US.						
	AN	United States Patent Application No. 10/797,972, entitled "Fabrication of Conductive Lines Interconnecting First Conductive Gates in Nonvolatile Memories Having Second Conductive Gates Provided By Conductive Gates Lines, Wherein The Adjacent Conductive Gate Lines For The Adjacent Columns Are Spaced From Each Other, And Non-Volatile Memory Structures," Filed on March 10, 2004; Attorney Docket No. M-15297 US.						
	AO							
	AP							
Examiner			Date Considered					
<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.</p>								